



IRF7807VD1 Information

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For Reference Only

Part Number IRF7807VD1

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

DescriptionMOSFET N-CH 30V 8.3A 8-SOIC**Package**8-SOIC (0.154", 3.90mm Width)

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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IRF7807VD1 Specifications

Manufacturer Part Number Manufacturer Infineon Technologies Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single Package Package 8-SOIC (0.154", 3.90mm Width) Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 8.3A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Schot Muster Schoff of Marter Scho		VDE5005VD 1
Category Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-SOIC (0.154", 3.90mm Width) Series FETKY? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) Current - Continuous Drain (Id) @ 25°C 8.3A (Ta) Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Schottky Diode (Isolated) Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Discrete Semiconductor Products Transistors - FETs, MOSFETs - Single 8-SOIC (0.154", 3.90mm Width) FETKY? FETKY? 8-SOIC (Mate Oxide) 1000		
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Current - Continuous Drain (Id) @ 25°C 8.3A (Ta) Drive Voltage (Max Rds On, Min Rds On) 4.5V Vgs(th) (Max) @ Id 3V @ 250µA Gate Charge (Qg) (Max) @ Vgs 14nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds - Vgs (Max) ±20V FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 25 mOhm @ 7A, 4.5V Operating Temperature -55°C ~ 150°C (TJ)	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On)4.5VVgs(th) (Max) @ Id3V @ 250μAGate Charge (Qg) (Max) @ Vgs14nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds-Vgs (Max)±20VFET FeatureSchottky Diode (Isolated)Power Dissipation (Max)2.5W (Ta)Rds On (Max) @ Id, Vgs25 mOhm @ 7A, 4.5VOperating Temperature-55°C ~ 150°C (TJ)	Drain to Source Voltage (Vdss)	30V
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FET Feature Schottky Diode (Isolated) Power Dissipation (Max) 2.5W (Ta) Rds On (Max) @ Id, Vgs 25 mOhm @ 7A, 4.5V Operating Temperature -55°C ~ 150°C (TJ)	Input Capacitance (Ciss) (Max) @ Vds	-
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Rds On (Max) @ Id, Vgs	FET Feature	Schottky Diode (Isolated)
Operating Temperature $-55^{\circ}\text{C} \sim 150^{\circ}\text{C} \text{ (TJ)}$	Power Dissipation (Max)	2.5W (Ta)
• • •	Rds On (Max) @ Id, Vgs	25 mOhm @ 7A, 4.5V
Mountain Town	Operating Temperature	-55°C ~ 150°C (TJ)
Mounting Type Surface Mount	Mounting Type	Surface Mount
Supplier Device Package 8-SO	Supplier Device Package	8-SO
Package / Case 8-SOIC (0.154", 3.90mm Width)	Package / Case	8-SOIC (0.154", 3.90mm Width)
Report errors?		Report errors?

IRF7807VD1 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRF7807VD1 Payment Methods



















IRF7807VD1 Shipping Methods













If you have any question about IRF7807VD1, please do not hesitate to contact us!

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